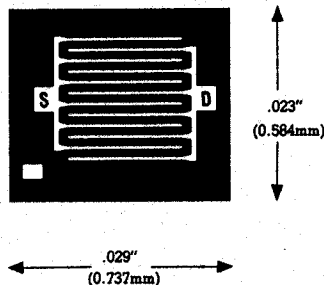


CHIP NUMBER

FP7.3



Die Size: 29 x 23 (mils)
0.737 x 0.584(mm)
3 x 3 (mils)
Pad Size: 0.076 x 0.076(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

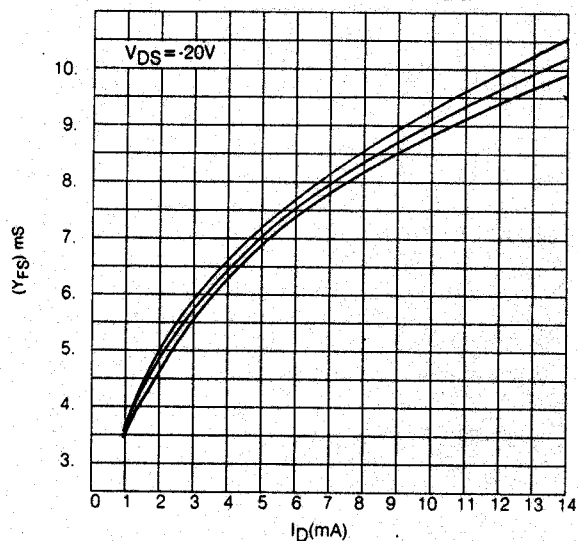
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
B _V GSS	25	40	50	V	V _{DS} = 0, I _G = 1μA
I _{DSS}	-5.0	-30	-120	mA	V _{DS} = -15V, V _{GS} = 0
g _{fs}		10		mmho	V _{DS} = -15V, V _{GS} = 0
I _{GSS}		50	500	pA	V _{GS} = 20V, V _{DS} = 0
r _{DS}	40	100	200	Ω	V _{DS} = 100mV, V _{GS} = 0
V _{GS(off)}	1.0	4.0	10	V	V _{DS} = -15V, I _D = 1nA
C _{rss}		4.5		pF	V _{DS} = 0, V _{GS} = 10V, f = 1MHz
C _{iss}		20	25	pF	V _{DS} = -15V, V _{GS} = 0, f = 1MHz

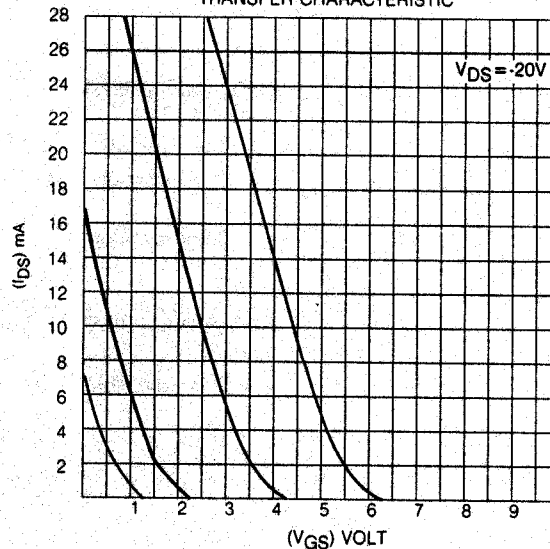
TYPICAL DEVICE TYPES: 2N5018, 2N5019, 2N5114 - 2N5116, 2N5319

CHIP TYPE FP7.3

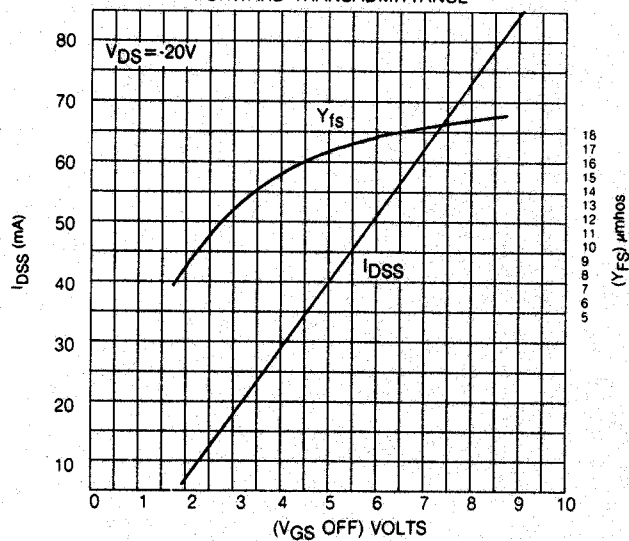
FORWARD TRANSADMITTANCE
VS. OPERATING DRAIN CURRENT



TRANSFER CHARACTERISTIC



FORWARD TRANSADMITTANCE



OUTPUT CHARACTERISTICS

